

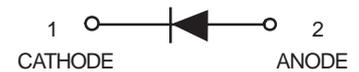
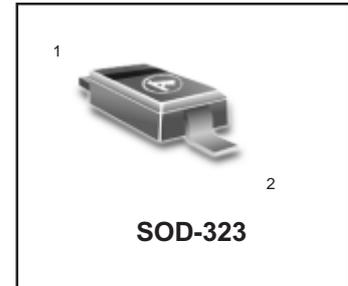
Schottky Barrier Diodes

These Schottky barrier diodes are designed for high speed switching applications, circuit protection, and voltage clamping. Extremely low forward voltage reduces conduction loss. Miniature surface mount package is excellent for hand held and portable applications where space is limited.

- Extremely Fast Switching Speed
- Low Forward Voltage — 0.35 Volts (Typ) @ $I_F = 10$ mAdc
- Device Marking: JV

We declare that the material of product compliance with RoHS requirements.

LBAT54HT1G



ORDERING INFORMATION

Device	Marking	Shipping
LBAT54HT1G	JV	3000/Tape & Reel
LBAT54HT3G	JV	10000/Tape & Reel

MAXIMUM RATINGS ($T_J = 125^\circ\text{C}$ unless otherwise noted)

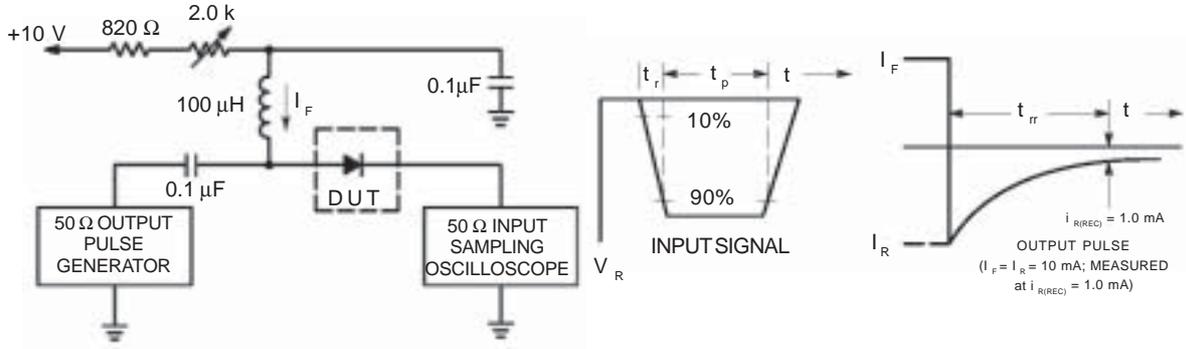
Rating	Symbol	Value	Unit
Reverse Voltage	V_R	30	V
Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board,* $T_A = 25^\circ\text{C}$	PD	200	mW
Derate above 25°C		1.57	mW/ $^\circ\text{C}$
Thermal Resistance Junction to Ambient	$R_{\theta JA}$	635	$^\circ\text{C/W}$
Junction Temperature	T_J	125Max	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	-55 to +150	$^\circ\text{C}$

* FR-4 Minimum Pad

ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (EACH DIODE)

Characteristic	Symbol	Min	Typ	Max	Unit
Reverse Breakdown Voltage ($I_R = 10 \mu\text{A}$)	$V_{(BR)R}$	30	—	—	Volts
Total Capacitance ($V_R = 1.0$ V, $f = 1.0$ MHz)	C_T	—	—	10	pF
Reverse Leakage ($V_R = 25$ V)	I_R	—	0.5	2.0	μAdc
Forward Voltage ($I_F = 0.1$ mAdc)	V_F	—	0.22	0.24	Vdc
Forward Voltage ($I_F = 0.15$ mAdc)	V_F	—	0.24	0.26	Vdc
Forward Voltage ($I_F = 0.15$ mAdc, $T_J = -25^\circ\text{C}$)	V_F	—	0.33	0.35	Vdc
Forward Voltage ($I_F = 0.15$ mAdc, $T_J = 85^\circ\text{C}$)	V_F	—	0.16	0.18	Vdc
Forward Voltage ($I_F = 30$ mAdc)	V_F	—	0.41	0.5	Vdc
Forward Voltage ($I_F = 100$ mAdc)	V_F	—	0.52	1.0	Vdc
Reverse Recovery Time ($I_F = I_R = 10$ mAdc, $I_{R(REC)} = 1.0$ mAdc, Figure 1)	t_{rr}	—	—	5.0	ns
Forward Voltage ($I_F = 1.0$ mAdc)	V_F	—	0.29	0.32	Vdc
Forward Voltage ($I_F = 10$ mAdc)	V_F	—	0.35	0.40	Vdc
Forward Current (DC)	I_F	—	—	200	mAdc
Repetitive Peak Forward Current	I_{FRM}	—	—	300	mAdc
Non-Repetitive Peak Forward Current ($t < 1.0$ s)	I_{FSM}	—	—	600	mAdc

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- Notes: 1. A 2.0 kΩ variable resistor adjusted for a Forward Current (I_F) of 10mA.
 2. Input pulse is adjusted so $I_{R(peak)}$ is equal to 10mA.
 3. $t_p \gg t_{rr}$

Figure 1. Recovery Time Equivalent Test Circuit

TYPICAL CHARACTERISTICS

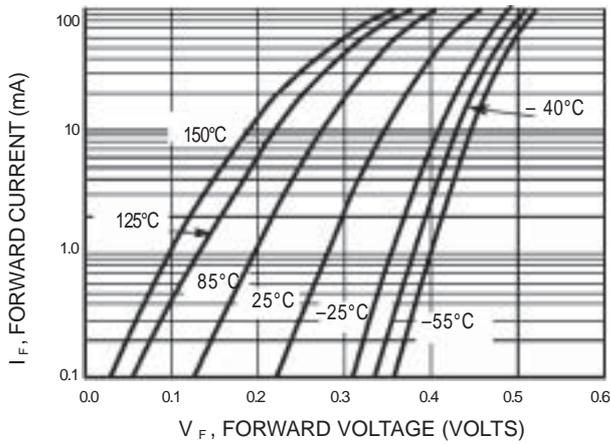


Figure 2. Forward Voltage

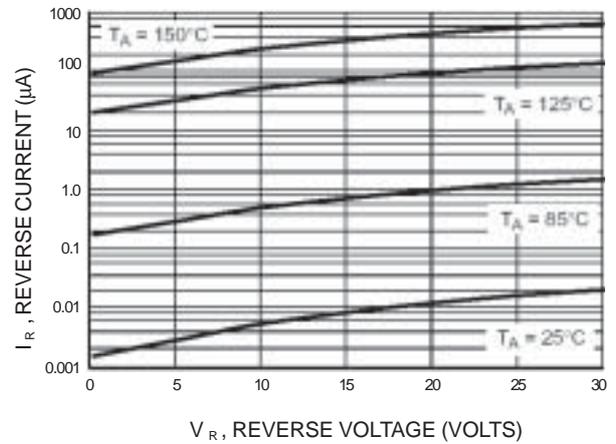


Figure 3. Leakage Current

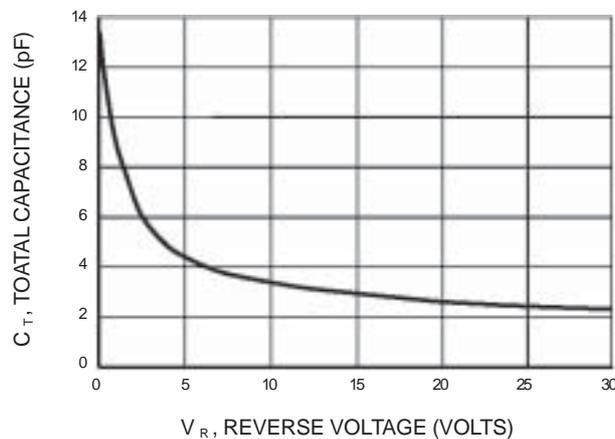
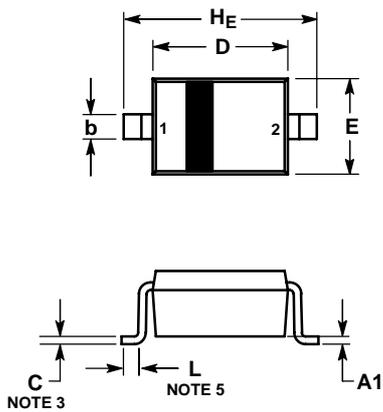


Figure 4. Total Capacitance

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SOD-323

NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: MILLIMETERS.
3. LEAD THICKNESS SPECIFIED PER L/F DRAWING WITH SOLDER PLATING.
4. DIMENSIONS A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS OR GATE BURRS.
5. DIMENSION L IS MEASURED FROM END OF RADIUS.

DIM	MILLIMETERS			INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A	0.80	0.90	1.00	0.031	0.035	0.040
A1	0.00	0.05	0.10	0.000	0.002	0.004
A3	0.15 REF			0.006 REF		
b	0.25	0.32	0.4	0.010	0.012	0.016
C	0.089	0.12	0.177	0.003	0.005	0.007
D	1.60	1.70	1.80	0.062	0.066	0.070
E	1.15	1.25	1.35	0.045	0.049	0.053
L	0.08			0.003		
HE	2.30	2.50	2.70	0.090	0.098	0.105

SOLDERING FOOTPRINT*
